Quad 2-Channel Multiplexer

The MC74VHC157 is an advanced high-speed CMOS quad 2-channel multiplexer, fabricated with silicon gate CMOS technology. It achieves high-speed operation similar to equivalent Bipolar-Schottky TTL, while maintaining CMOS low-power dissipation.

It consists of four 2-input digital multiplexers with common select (S) and enable (\overline{E}) inputs. When \overline{E} is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 4.1 \text{ ns (Typ)}$ at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25$ °C
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 82 FETs
- These devices are available in Pb-free package(s). Specifications herein
 apply to both standard and Pb-free devices. Please see our website at
 www.onsemi.com for specific Pb-free orderable part numbers, or
 contact your local ON Semiconductor sales office or representative.

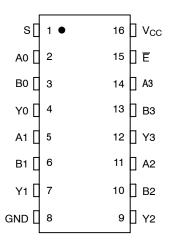


Figure 1. Pin Assignment



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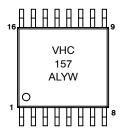
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MARKING DIAGRAMS

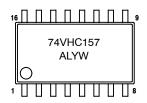












A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74VHC157D	SOIC-16	48 Units/Rail
MC74VHC157DR2	SOIC-16	2500 Units/Reel
MC74VHC157DT	TSSOP-16	96 Units/Rail
MC74VHC157DTR2	TSSOP-16	2500 Units/Reel
MC74VHC157M	SOIC EIAJ-16	50 Units/Rail
MC74VHC157MEL	SOIC EIAJ-16	2000 Units/Reel

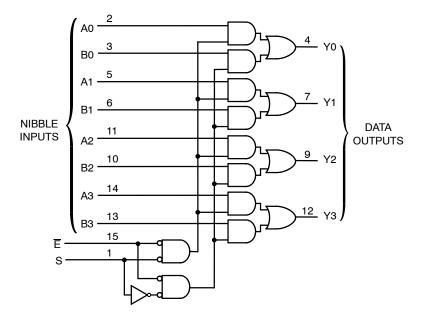


Figure 2. Expanded Logic Diagram

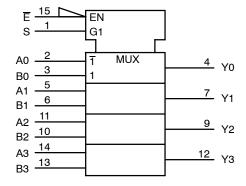


Figure 3. IEC Logic Symbol

FUNCTION TABLE

Inp	Outputs	
E	s	Y0 - Y3
Н	Х	L
L	L	A0-A3
L	Н	B0-B3

A0 - A3, B0 - B3 = the levels of the respective Data-Word Inputs.

MAXIMUM RATINGS (Note 1)

Symbol	Parame	ter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		-0.5 to $V_{CC} + 7.0$	V
Vo	DC Output Voltage		-0.5 to $V_{CC} + 7.0$	V
I _{IK}	DC Input Diode Current	$V_I < GND$	-20	mA
I _{OK}	DC Output Diode Current	V _O < GND	±20	mA
Io	DC Output Sink Current		± 25	mA
I _{CC}	DC Supply Current per Supply Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 S	Seconds	260	°C
T_{J}	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance		250	°C/W
P_{D}	Power Dissipation in Still Air at 85°C		250	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% - 35%	UL-94-VO (0.125 in)	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	V
I _{Latch-Up}	Latch-Up Performance Abov	e V _{CC} and Below GND at 85°C (Note 5)	±500	mA

^{1.} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum-rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{IN}	DC Input Voltage (Note 6)	0	5.5	V
V _{OUT}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature Range, all Package Types	- 55	125	°C
t _r , t _f	Input Rise or Fall Time $ \begin{array}{c} V_{CC} = 3.3 \ V \ \pm \ 0.3 \ V \\ V_{CC} = 5.0 \ V \ \pm \ 0.5 \ V \end{array} $	0 0	100 20	ns/V

^{6.} Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	100 178,700	
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

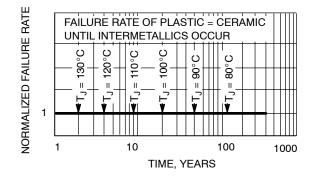


Figure 4. Failure Rate vs. Time Junction Temperature

^{2.} Tested to EIA/JESD22-A114-A.

^{3.} Tested to EIA/JESD22-A115-A.

^{4.} Tested to JESD22-C101-A.

Tested to EIA/JESD78.

DC CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	Т	A = 25°(T _A ≤	85°C	-55°C ≤T	A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 to 5.5	1.5 0.7 V _{CC}			1.5 0.7 V _{CC}		1.5 0.7 V _{CC}		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 to 5.5			0.5 0.3 V _{CC}		0.5 0.3 V _{CC}		0.5 0.3 V _{CC}	V
V _{OH}	High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.8		2.34 3.66		
V _{OL}	Low-Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = 4$ mA $I_{OH} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			± 0.1		±1.0		±1.0	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			4.0		40.0		40.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

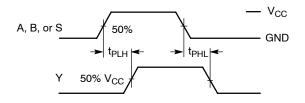
					T _A = 25°	С	T _A ≤85°C -55°C ≤T _A ≤125°C		_A ≤125°C		
Symbol	Characteristic	Test Condit	ions	Min	Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay, A to B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		6.2 8.7	9.7 13.2	1.0 1.0	11.5 15.0	1.0 1.0	11.5 15.0	ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15 pF$ $C_L = 50 pF$		4.1 5.6	6.4 8.4	1.0 1.0	7.5 9.5	1.0 1.0	7.5 9.5	
t _{PLH} , t _{PHL}	Propagation Delay, S to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		8.4 10.9	13.2 16.7	1.0 1.0	15.5 19.0	1.0 1.0	15.5 19.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		5.3 6.8	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t _{PLH} , t _{PHL}	Propagation Delay, E to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		8.7 11.2	13.6 17.1	1.0 1.0	16.0 19.5	1.0 1.0	16.0 19.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		5.6 7.1	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	
C _{IN}	Input Capacitance				4	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 7)	20	pF

^{7.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$ is used to determine the no-load dynamic power consumption: $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}; C_L = 50 \text{ pF}; V_{CC} = 5.0 \text{ V})$

		T _A = 3		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	8.0	٧
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	٧
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V



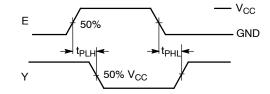
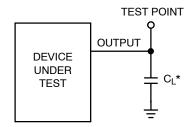


Figure 5. Switching Waveform

Figure 6. Inverting Switching



^{*}Includes all probe and jig capacitance.

Figure 7. Test Circuit

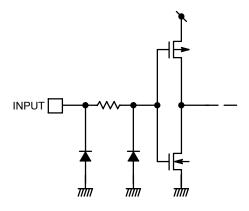
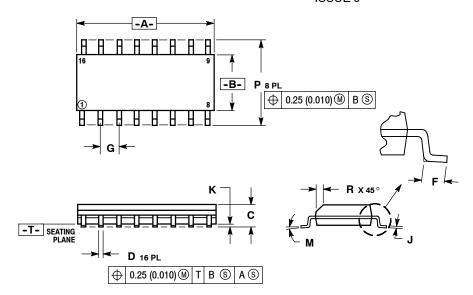


Figure 8. Input Equivalent Circuit

PACKAGE DIMENSIONS

SOIC-16 D SUFFIX CASE 751B-05 **ISSUE J**

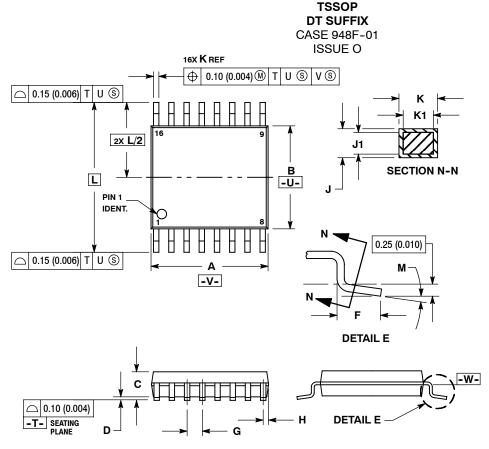


NOTES:

- NOTES:
 1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2 CONTROLLING DIMENSION: MILLIMETER.
 3 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4 MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	9.80	10.00	0.386	0.393		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27	BSC	0.050 BSC			
J	0.19	0.25	0.008	0.009		
K	0.10	0.25	0.004	0.009		
М	0°	7°	0°	7°		
Р	5.80	6.20	0.229	0.244		
R	0.25	0.50	0.010	0.019		



NOTES:

- 11. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (0.006) PER SIDE.

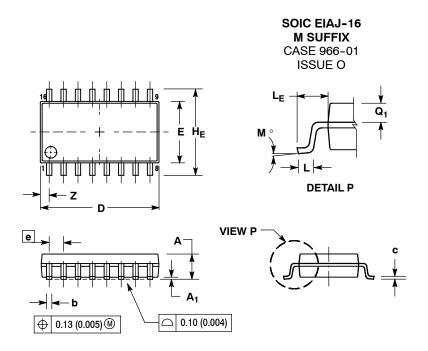
 DIMENSION B DOES NOT INCLUDE INTERLEAD
 FLASH OR PROTRUSION. INTERLEAD FLASH OR
 PROTRUSION SHALL NOT EXCEED
 0.25 (0.010) PER SIDE.

 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION. SHALL BE OR 10 (202) TOTAL IN
- PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	6.40 BSC		BSC	
М	0°	8°	0°	8°	

PACKAGE DIMENSIONS



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD
 FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	,	,		
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
ᄪ	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q_1	0.70	0.90	0.028	0.035
Z		0.78		0.031

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